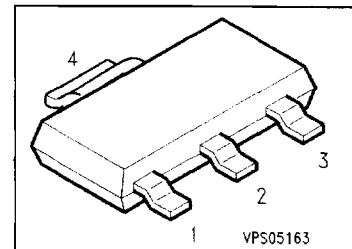
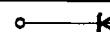


Silicon Switching Diodes

BAS 78 A
... **BAS 78 D**

- Switching applications
- High breakdown voltage



Type	Marking	Ordering Code (tape and reel)	Pin Configuration	Package ¹⁾
BAS 78 A	BAS 78 A	Q62702-A910	o —  — o	SOT-223
BAS 78 B	BAS 78 B	Q62702-A911	2,4	1
BAS 78 C	BAS 78 C	Q62702-A912		
BAS 78 D	BAS 78 D	Q62702-A913		

Maximum Ratings

Parameter	Symbol	Values				Unit
		BAS 78 A	BAS 78 B	BAS 78 C	BAS 78 D	
Reverse voltage	V_R	50	100	200	400	V
Peak reverse voltage	V_{RM}	50	100	200	400	
Forward current	I_F		1			A
Peak forward current	I_{FM}		1			
Surge forward current, $t = 1 \mu\text{s}$	I_{FS}		10			
Total power dissipation, $T_S = 124^\circ\text{C}^2$	P_{tot}		1.2			W
Junction temperature	T_j		150			$^\circ\text{C}$
Storage temperature range	T_{stg}		– 65 ... + 150			

Thermal Resistance

Junction - ambient ²⁾	$R_{th JA}$	≤ 92	K/W
Junction - soldering point	$R_{th JS}$	≤ 22	

1) For detailed information see chapter Package Outlines.

2) Package mounted on epoxy pcb 40 mm × 40 mm × 1.5 mm/6 cm² Cu.

Electrical Characteristicsat $T_A = 25^\circ\text{C}$, unless otherwise specified.

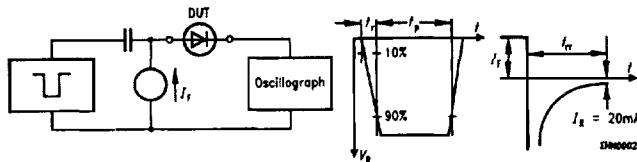
Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC characteristics

Breakdown voltage $I_{(BR)} = 100 \mu\text{A}$	$V_{(BR)}$	50	—	—	V
BAS 78 A		100	—	—	
BAS 78 B		200	—	—	
BAS 78 C		400	—	—	
BAS 78 D		—	—	—	
Forward voltage ¹⁾ $I_F = 1 \text{ A}$ $I_F = 2 \text{ A}$	V_F	—	—	1.6	
Reverse current $V_R = V_{R \text{ max}}$ $V_R = V_{R \text{ max}}, T_A = 150^\circ\text{C}$	I_R	—	—	1	μA
		—	—	50	

AC characteristics

Diode capacitance $V_R = 0, f = 1 \text{ MHz}$	C_D	—	10	—	pF
Reverse recovery time $I_F = 200 \text{ mA}, I_R = 200 \text{ mA}, R_L = 100 \Omega$ measured at $I_R = 20 \text{ mA}$	t_{rr}	—	1	—	μs

Test circuit for reverse recovery time

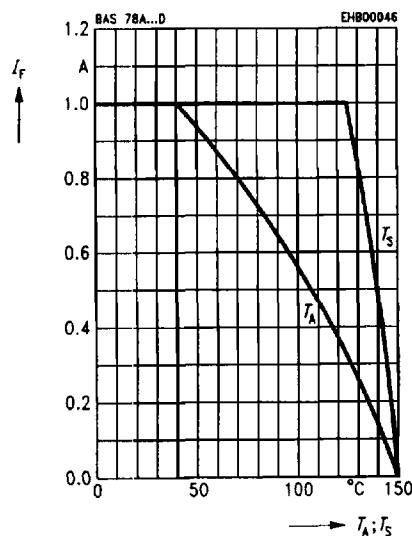
Pulse generator: $t_p = 5 \mu\text{s}$, $D = 0.05$
 $t_r = 0.6 \text{ ns}$, $R_j = 50 \Omega$
 $V_p = V_R + I_F \times R_j$

Oscilloscope: $R = 50 \Omega$
 $t_r = 0.35 \text{ ns}$
 $C \leq 1 \text{ pF}$

1) Pulse test conditions: $t \leq 300 \mu\text{s}$, $D = 2 \%$.

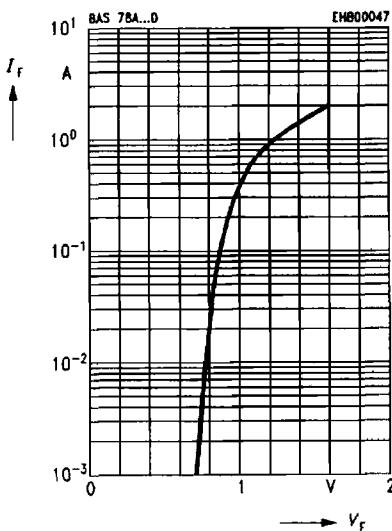
Forward current $I_F = f(T_A^*; T_S)$

* Package mounted on epoxy



Forward current $I_F = f(V_F)$

$T_A = 25^\circ\text{C}$



Reverse current $I_R = f(T_A)$

$V_{CE} = 10$ V

